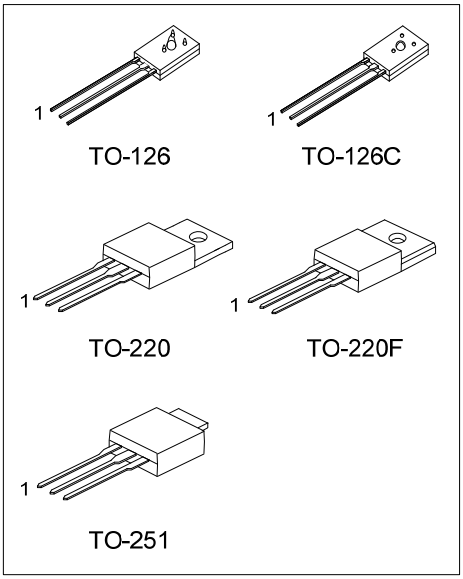
2SC5353B

NPN SILICON TRANSISTOR

HIGH VOLTAGE NPN TRANSISTOR



■ DESCRIPTION

Switching Regulator and High Voltage Switching Applications
High-Speed DC-DC Converter Applications

■ FEATURES

* Excellent switching times: t_R = 0.7μs$_{(MAX)}$, t_F = 0.5μs $_{(MAX)}$
* High collectors breakdown voltage: V_{CEO} = 750V

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC5353BL-T60-K	2SC5353BG-T60-K	TO-126	B	C	E	Bulk
2SC5353BL-T6C-K	2SC5353BG-T6C-K	TO-126C	B	C	E	Bulk
2SC5353BL-TA3-T	2SC5353BG-TA3-T	TO-220	B	C	E	Tube
2SC5353BL-TF3-T	2SC5353BG-TF3-T	TO-220F	B	C	E	Tube
2SC5353BL-TM3-T	2SC5353BG-TM3-T	TO-251	B	C	E	Tube

2SC5353BL-TA3-T
(1)Packing Type
(2)Package Type
(3)Lead Plating

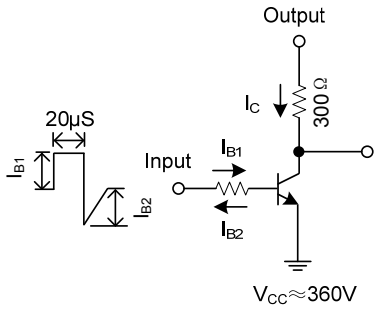
(1) K: Bulk, T: Tube
(2) T60: TO-126, T6C: TO-126C, TA3: TO-220, TF3: TO-220F, TM3: TO-251
(3) G: Halogen Free, L: Lead Free Plating

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	900	V
Collector-Emitter Voltage		V_{CEO}	750	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	3	A
	Pulse	I_{CP}	5	A
Base Current		I_B	1	A
Collector Power Dissipation	TO-220F/TO-126/TO-126C	P_D	20	W
	TO-220/TO-251		25	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

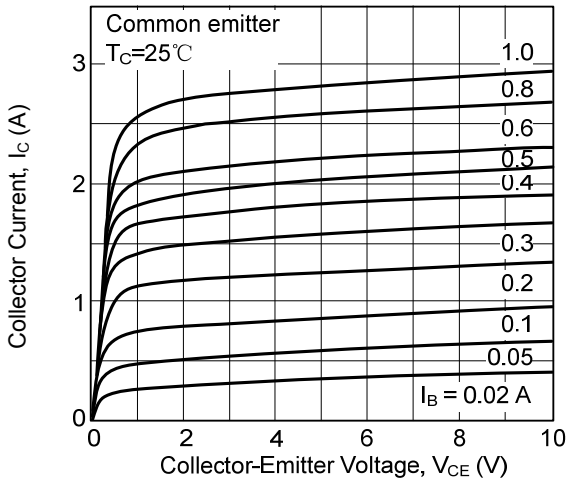
Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_C = 25°C)

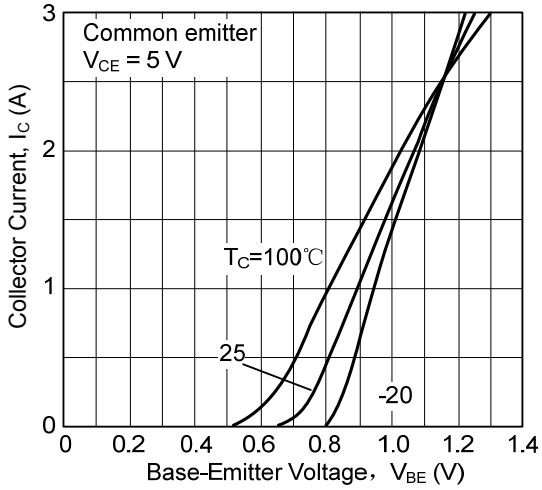
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage		BV_{CBO}	I_C=1 mA, I_E = 0	900			V
Collector-Emitter Breakdown Voltage		BV_{CEO}	I_C=10 mA, I_B = 0	750			V
Collector Cut-off Current		I_{CBO}	V_{CB}=720V, I_E= 0			100	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=7V, I_C= 0			10	μA
DC Current Gain		h_{FE1}	V_{CE}=5 V, I_C=1 mA	10			
		h_{FE2}	V_{CE}=5 V, I_C=0.15 A	15			
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	I_C=1.2 A, I_B=0.24 A			1.0	V
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$	I_C=1.2 A, I_B=0.24 A			1.3	V
Switching Time	Rise Time	t_R				0.7	μS
	Storage Time	t_{STG}				4.0	μS
	Fall Time	t_F	I_{B1} = 0.24 A, I_{B2} = −0.48 A, duty cycle ≤ 1%			0.5	μS

■ TYPICAL CHARACTERISTICS

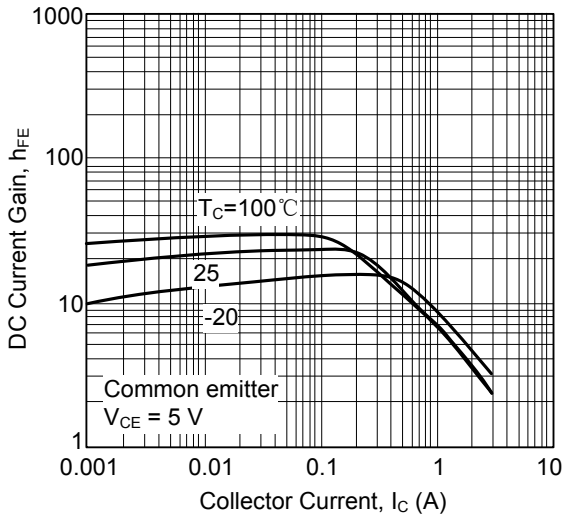
Collector Current vs. Collector-Emitter Voltage



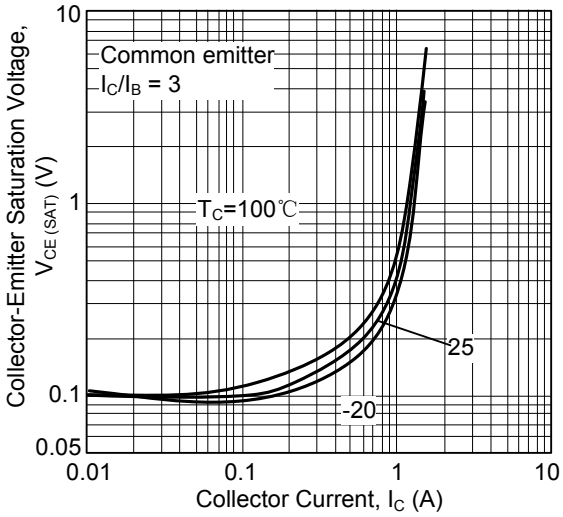
Collector Current vs. Base-Emitter Voltage



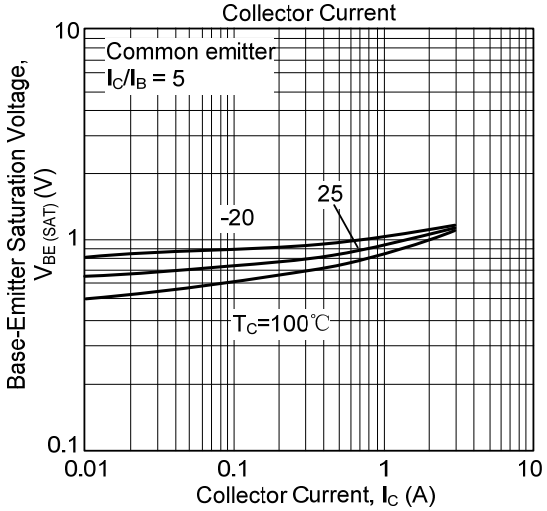
DC Current Gain vs. Collector Current



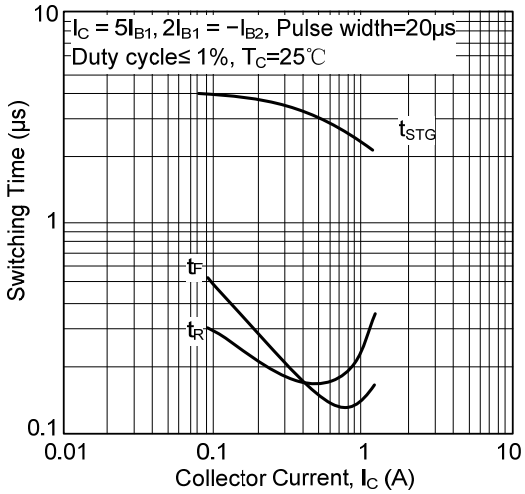
Collector-Emitter Saturation Voltage vs. Collector Current



Base-Emitter Saturation Voltage vs. Collector Current



Switching Characteristics



■ TYPICAL CHARACTERISTICS(Cont.)